

IN THE CLAIMS

Please amend claims 1, 15 and cancel claim 6, all without prejudice as follows.

What is claimed is:

1. (Currently Amended) A programmable device, comprising:

a substrate-~~(10)~~;

an insulator-~~(13)~~ on said substrate;

an elongated semiconductor material-~~(12)~~ on said insulator, said elongated semiconductor material having first and second ends, and an upper surface-~~S~~,

said first end-~~(12a)~~ being substantially wider than said second end-~~(12b)~~ and comprising a plurality of integral triangular-shaped portions forming openings which face generally toward said second end, and

a metallic material on said upper surface, said metallic material being physically migratable along said upper surface responsive to an electrical current-~~I~~ flowable through said semiconductor material and through said metallic material.

2. (Original) The programmable device as claimed in claim 1,

further comprising an energy source connected to said elongated semiconductor material, for causing an electrical current to flow through said elongated semiconductor material and through said metallic material, and for causing said metallic material to migrate along said upper surface.

3. (Original) The programmable device as claimed in claim 1, wherein said elongated semiconductor material comprises a doped polysilicon.

4. (Original) The programmable device as claimed in claim 1, wherein said metallic material comprises a metallic silicide.

5. (Original) The programmable device as claimed in claim 1, wherein said metallic material is a metallic silicide selected from the group consisting of WSi_2 , NiSi_2 and CoSi_2 .

6. (Cancelled) The programmable device as claimed in claim 1, wherein said first end comprises a plurality of integral triangular-shaped portions.

7. (Original) The programmable device as claimed in claim 1, wherein said second end comprises an oblong-shaped portion.

8. (Original) The programmable device as claimed in claim 1, wherein said metallic material is disposed on the entire upper surface of said elongated semiconductor material.